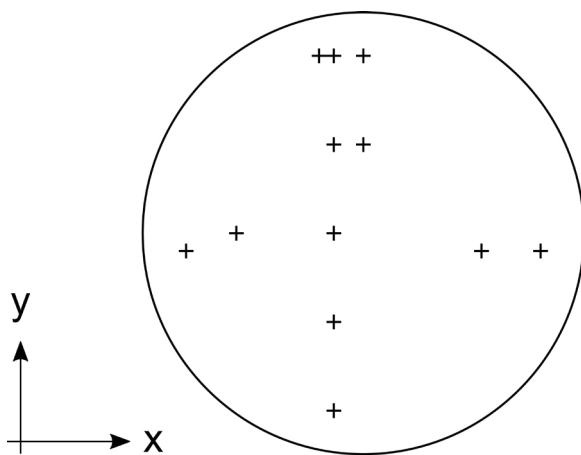


Magnetron Sputtering Uniformity Data

Overview:

Magnetron sputtering was carried out using Moorfield MAGNETRON sources with 3" targets, arranged in a confocal manner in a Moorfield MiniLab deposition system. Substrates were 6" diameter polished wafers that were rotated during deposition. Thickness measurements were by surface profilometry.

SiO₂ Deposition (RF):

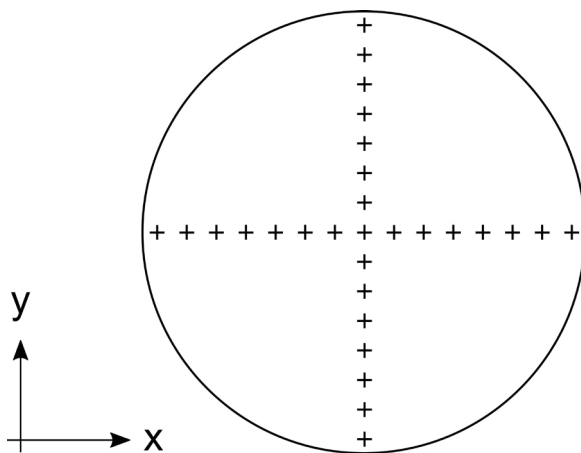


x (mm)	y (mm)	Thickness (Å)
-10	0	597
-10	-30	599
-10	-60	588
-10	30	599
-10	60	596
-43	0	596
-60	-6	588
40	-6	596
60	-6	586
0	30	600
0	60	575
-15	60	585

Power: 150 W (RF); Time: 40 minutes

Non-uniformity: ±2.1%

Ti Deposition (DC):



x sweep (mm)	Thickness (Å)	y sweep (mm)	Thickness (Å)
70	4450	70	4580
60	4285	60	4440
50	4320	50	4300
40	4330	40	4400
30	4295	30	4300
20	4290	20	4340
10	4240	10	4390
0	4290	0	4290
-10	4380	-10	4260
-20	4340	-20	4380
-30	4340	-30	4400
-40	4315	-40	4430
-50	4340	-50	4470
-60	4375	-60	4290
-70	4630	-70	4480

Power: 540 W (DC); Time: 30 minutes

Non-uniformity: ±4.5%